

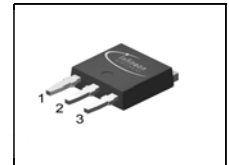
**Cool MOS™ Power Transistor**
**Feature**

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Pb-free lead plating; RoHS compliant; available in Halogen free mold compound<sup>a)</sup>
- Qualified according to JEDEC<sup>0)</sup> for target applications

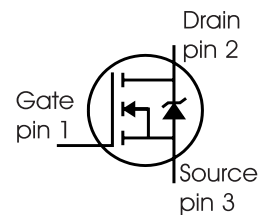
$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	3	$\Omega$
$I_D$	1.8	A



PG-TO251-3-11



Type	Package	Ordering Code	Marking
SPS02N60C3	PG-TO251-3-11	-	02N60C3


**Maximum Ratings**

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	$I_D$	1.8 1.1	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\text{ puls}}$	5.4	
Avalanche energy, single pulse $I_D = 1.35\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AS}$	50	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1)</sup> $I_D = 1.8\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AR}$	0.07	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	1.8	A
Gate source voltage static	$V_{GS}$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	
Power dissipation, $T_C = 25\text{ °C}$	$P_{tot}$	25	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^{\circ}\text{C}$
Reverse diode dv/dt <sup>5)</sup>	dv/dt	15	V/ns

<sup>a)</sup> non-Halogen free (OPN: SPS02N60C3BT); Halogen free (OPN: SPS02N60C3AT)

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480 \text{ V}$ , $I_D = 1.8 \text{ A}$ , $T_j = 125 \text{ }^\circ\text{C}$	$dv/dt$	50	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	5	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	75	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	75 50	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	$^\circ\text{C}$

**Electrical Characteristics, at  $T_j=25^\circ\text{C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$ , $I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$ , $I_D=0.25\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=80\mu\text{A}$ , $V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=25^\circ\text{C}$ , $T_j=150^\circ\text{C}$	-	0.5	1 50	$\mu\text{A}$
Gate-source leakage current	$I_{GSS}$	$V_{GS}=30\text{V}$ , $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ , $I_D=1.1\text{A}$ , $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	2.7 7.3	3 -	$\Omega$
Gate input resistance	$R_G$	$f=1\text{MHz}$ , open Drain	-	9	-	

**Electrical Characteristics** , at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 1.1\text{A}$	-	1.75	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	200	-	pF
Output capacitance	$C_{oss}$		-	90	-	
Reverse transfer capacitance	$C_{rss}$		-	4	-	
Effective output capacitance, <sup>3)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V to } 480\text{V}$	-	8.1	-	pF
Effective output capacitance, <sup>4)</sup> time related	$C_{o(tr)}$		-	15.7	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350\text{V}$ , $V_{GS} = 0/10\text{V}$ , $I_D = 1.8\text{A}$ , $R_G = 25\Omega$	-	6	-	ns
Rise time	$t_r$		-	3	-	
Turn-off delay time	$t_{d(off)}$		-	68	70	
Fall time	$t_f$		-	12	30	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 420\text{V}$ , $I_D = 1.8\text{A}$	-	1.6	-	nC
Gate to drain charge	$Q_{gd}$		-	3.8	-	
Gate charge total	$Q_g$	$V_{DD} = 420\text{V}$ , $I_D = 1.8\text{A}$ , $V_{GS} = 0\text{ to } 10\text{V}$	-	9.5	12.5	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 420\text{V}$ , $I_D = 1.8\text{A}$	-	5.5	-	V

<sup>0</sup>J-STD20 and JESD22

<sup>1</sup>Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

<sup>3</sup> $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>4</sup> $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

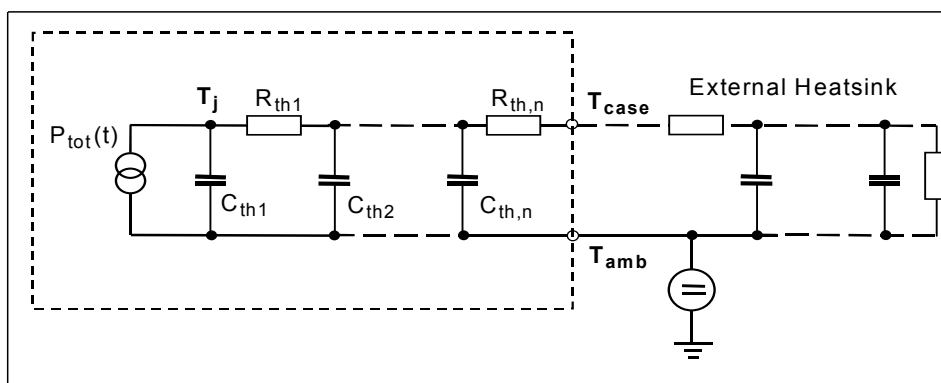
<sup>5</sup> $I_{SD} \leq I_D$ ,  $di/dt \leq 400\text{A}/\mu\text{s}$ ,  $V_{DClink} = 400\text{V}$ ,  $V_{peak} < V_{BR, DSS}$ ,  $T_j < T_{j,max}$ .  
Identical low-side and high-side switch.

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	1.8	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	5.4	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=420\text{V}, I_F=I_S,$	-	200	350	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	1.3	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	9	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$		-	-	200	$\text{A}/\mu\text{s}$

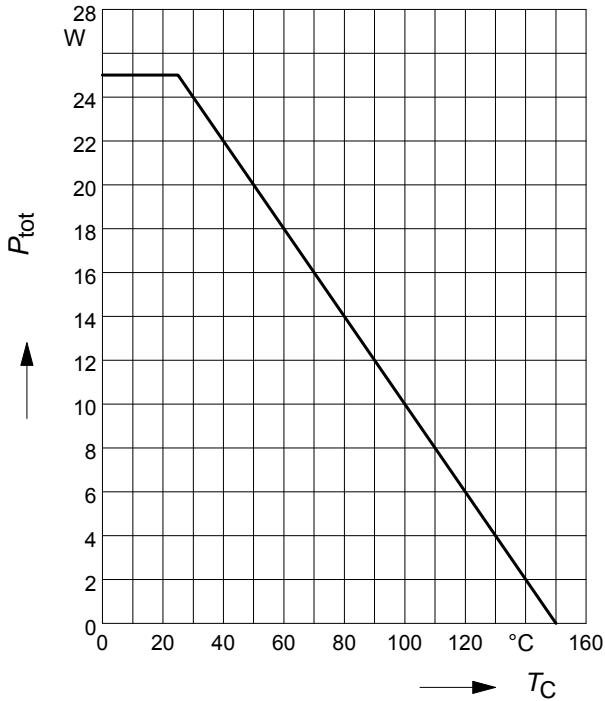
**Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
$R_{th1}$	0.1	K/W	$C_{th1}$	0.00002806	Ws/K
$R_{th2}$	0.184		$C_{th2}$	0.0001113	
$R_{th3}$	0.306		$C_{th3}$	0.0001679	
$R_{th4}$	1.207		$C_{th4}$	0.000547	
$R_{th5}$	0.974		$C_{th5}$	0.001388	
$R_{th6}$	0.251		$C_{th6}$	0.019	



**1 Power dissipation**

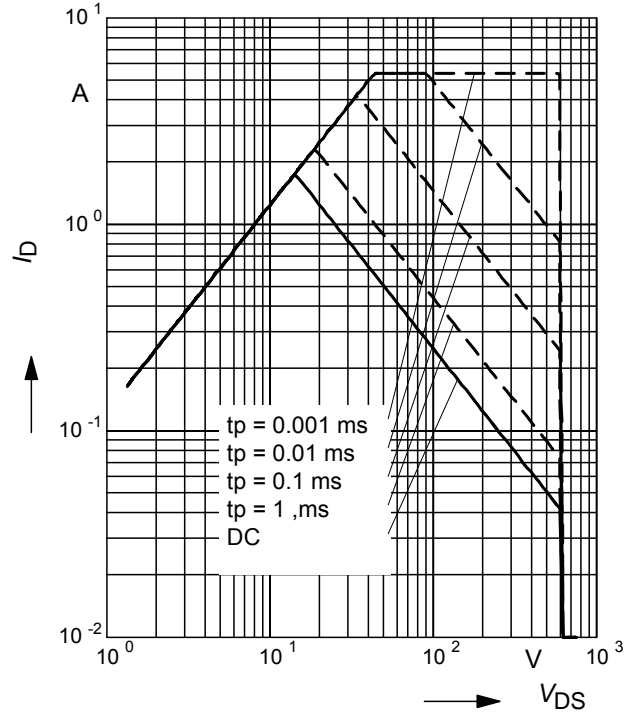
$P_{tot} = f(T_C)$



**2 Safe operating area**

$I_D = f(V_{DS})$

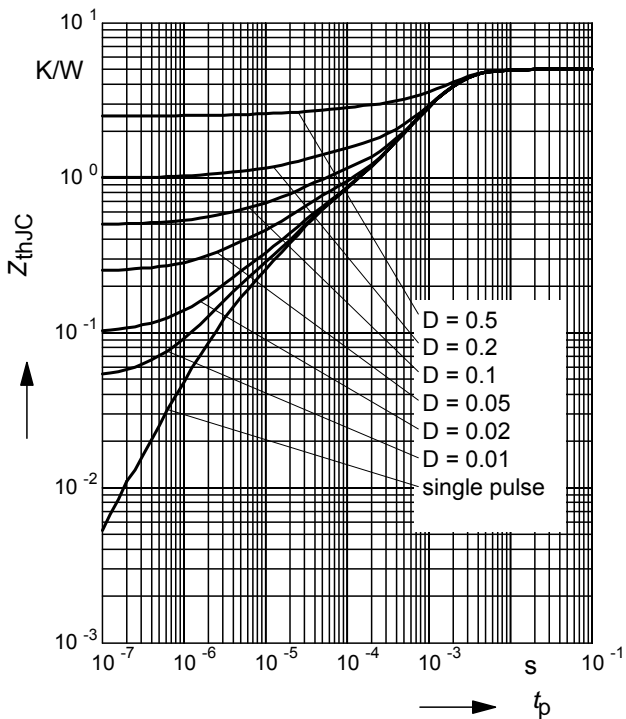
parameter :  $D = 0$  ,  $T_C = 25^\circ C$



**3 Transient thermal impedance**

$Z_{thJC} = f(t_p)$

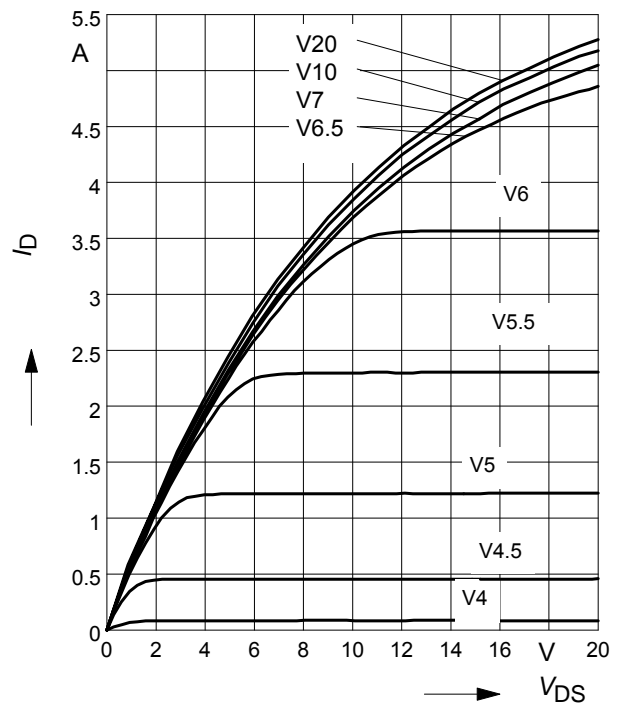
parameter:  $D = t_p/T$



**4 Typ. output characteristic**

$I_D = f(V_{DS})$ ;  $T_j = 25^\circ C$

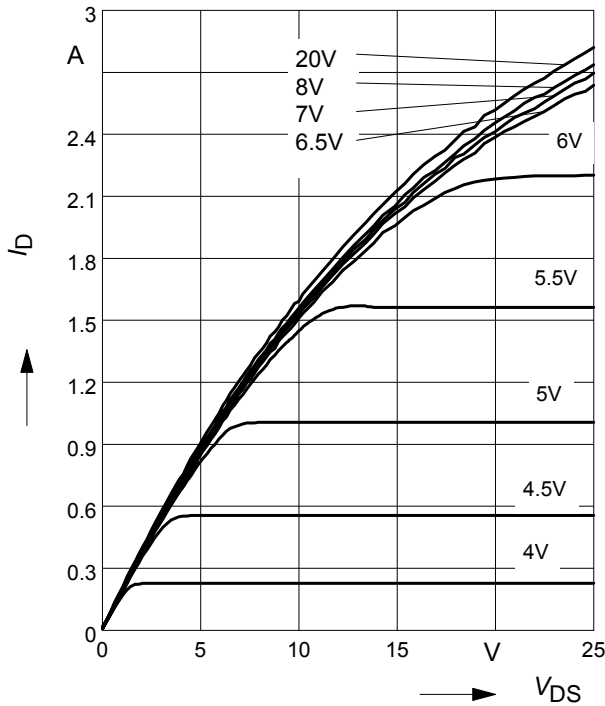
parameter:  $t_p = 10 \mu s$ ,  $V_{GS}$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

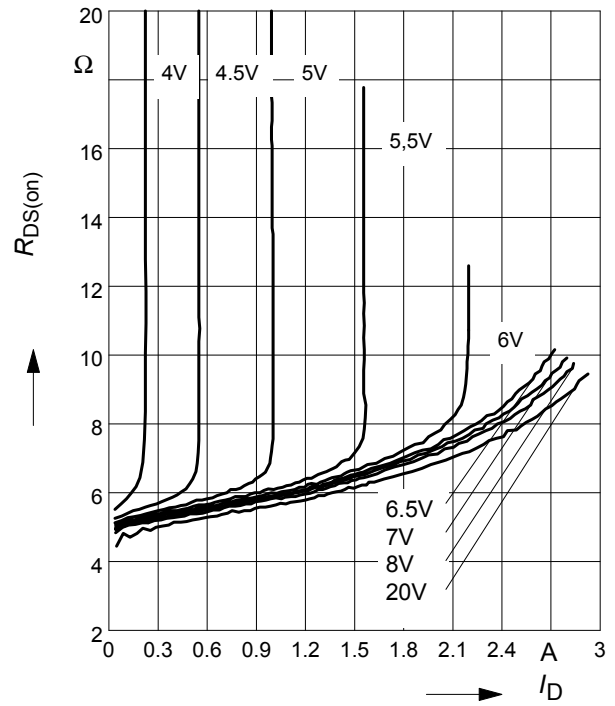
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

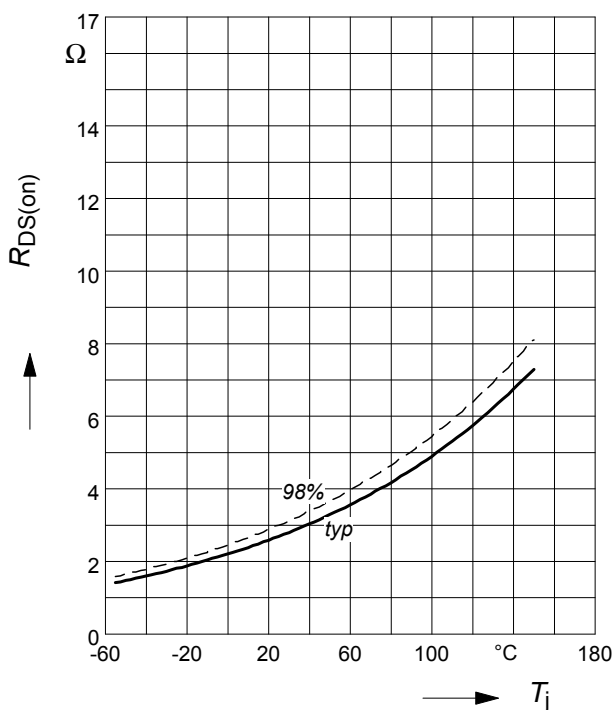
parameter:  $T_j = 150^\circ\text{C}, V_{GS}$



**7 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j)$

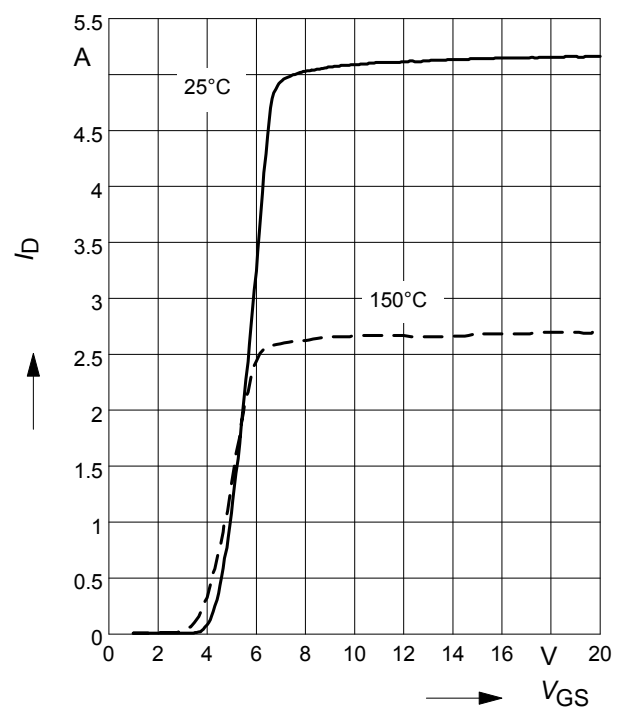
parameter:  $I_D = 1.1 \text{ A}, V_{GS} = 10 \text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

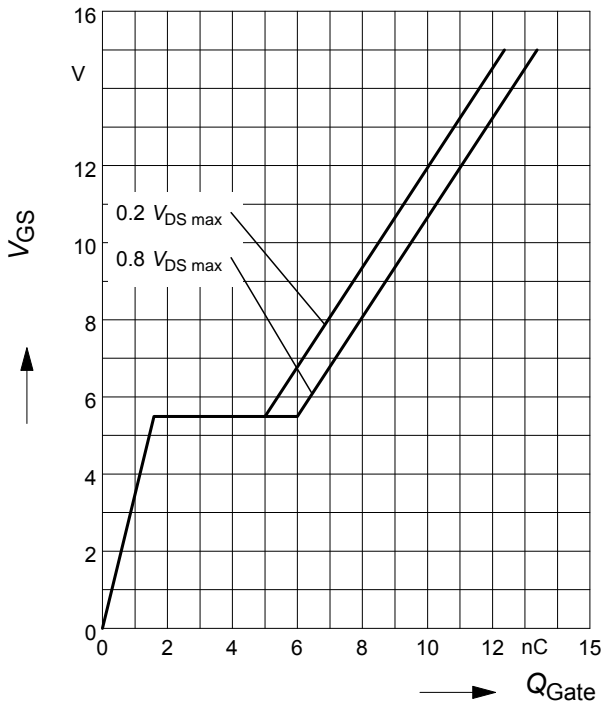
parameter:  $t_p = 10 \mu\text{s}$



**9 Typ. gate charge**

$V_{GS} = f(Q_{Gate})$

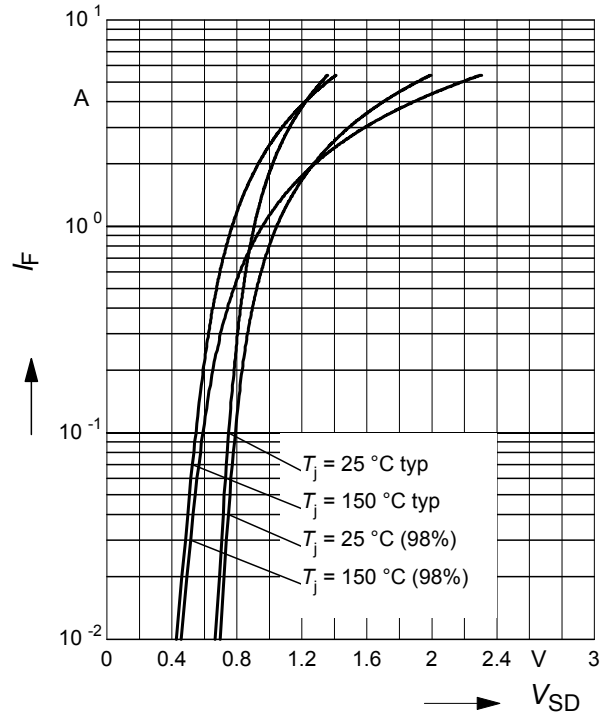
parameter:  $I_D = 1.8\text{ A}$  pulsed



**10 Forward characteristics of body diode**

$I_F = f(V_{SD})$

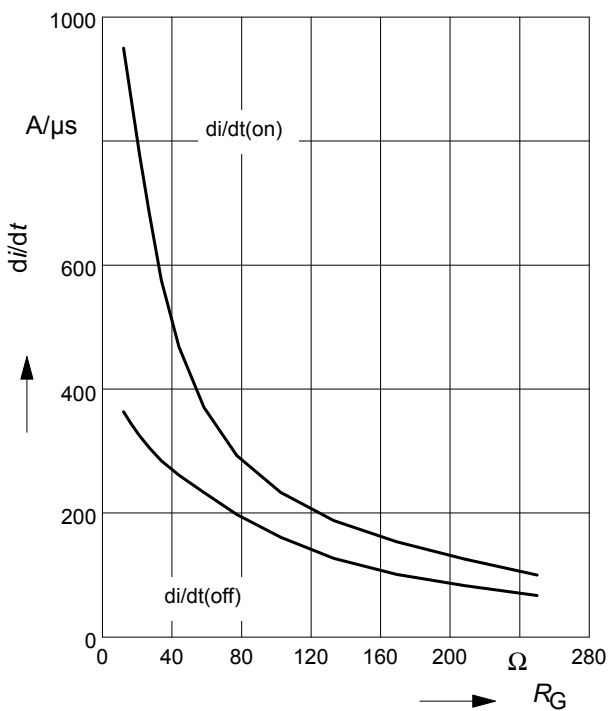
parameter:  $T_j, t_p = 10\ \mu\text{s}$



**11 Typ. drain current slope**

$di/dt = f(R_G)$ , inductive load,  $T_j = 125\text{ °C}$

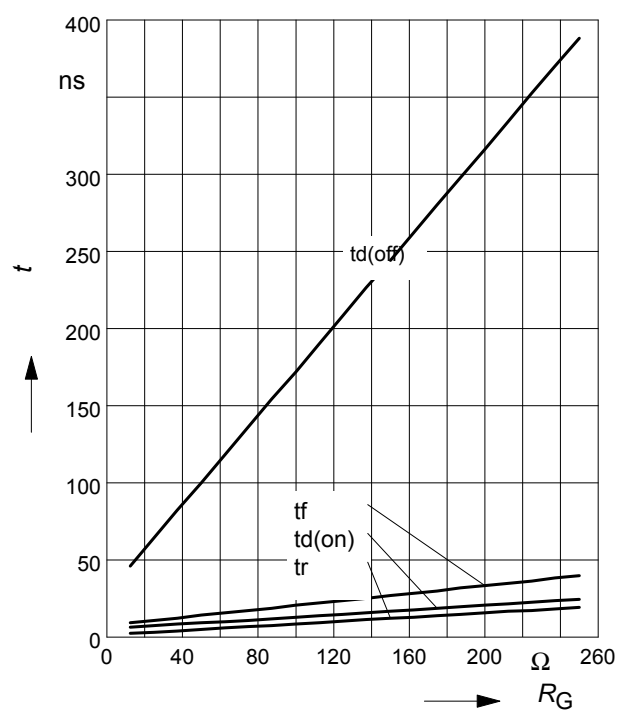
par.:  $V_{DS}=380\text{V}, V_{GS}=0/+13\text{V}, I_D=1.8\text{A}$



**12 Typ. switching time**

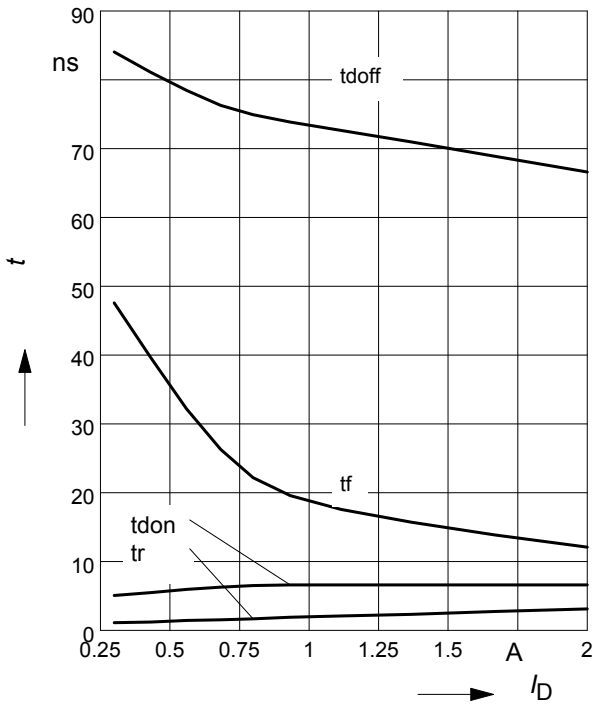
$t = f(R_G)$ , inductive load,  $T_j=125\text{ °C}$

par.:  $V_{DS}=380\text{V}, V_{GS}=0/+13\text{V}, I_D=1.8\text{ A}$



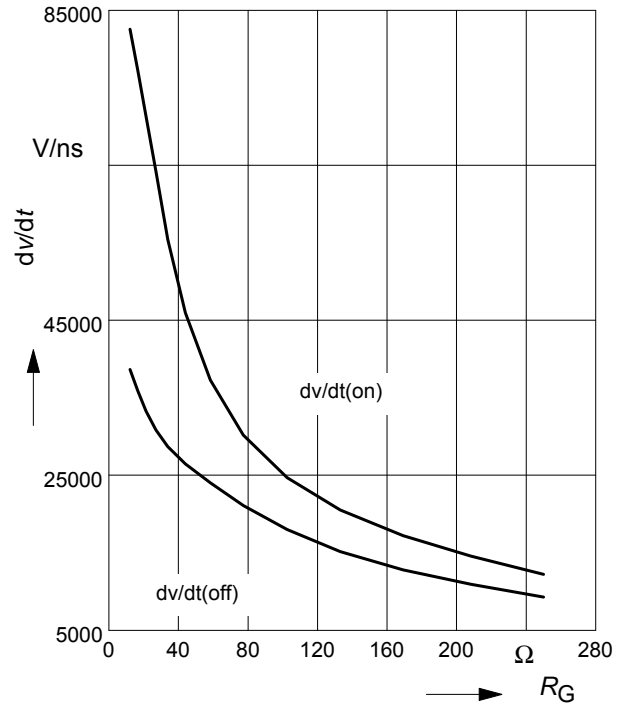
**13 Typ. switching time**

$t = f(I_D)$ , inductive load,  $T_j=125^\circ\text{C}$   
 par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $R_G=25\Omega$



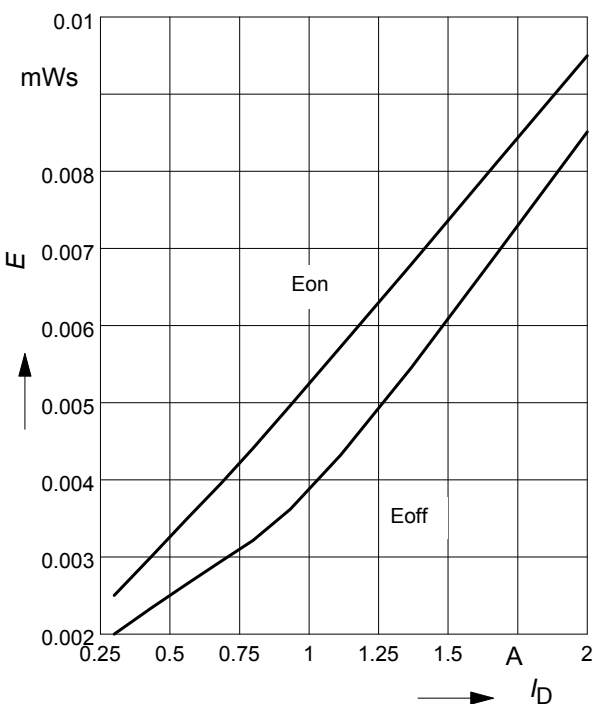
**14 Typ. drain source voltage slope**

$dv/dt = f(R_G)$ , inductive load,  $T_j = 125^\circ\text{C}$   
 par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $I_D=1.8\text{A}$



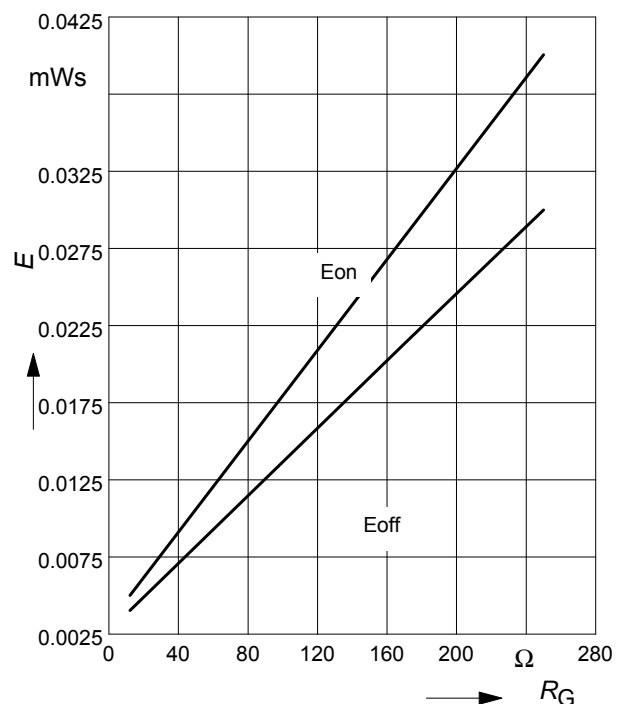
**15 Typ. switching losses**

$E = f(I_D)$ , inductive load,  $T_j=125^\circ\text{C}$   
 par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $R_G=25\Omega$



**16 Typ. switching losses**

$E = f(R_G)$ , inductive load,  $T_j=125^\circ\text{C}$   
 par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $I_D=1.8\text{A}$

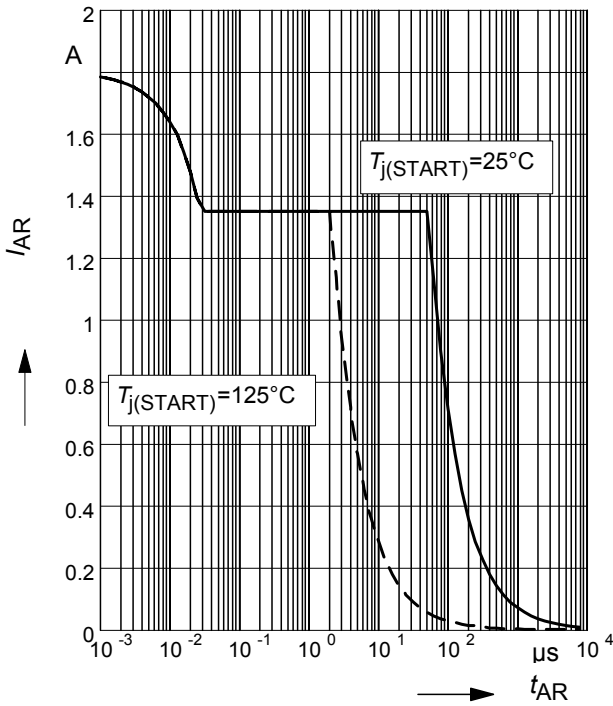




**17 Avalanche SOA**

$I_{AR} = f(t_{AR})$

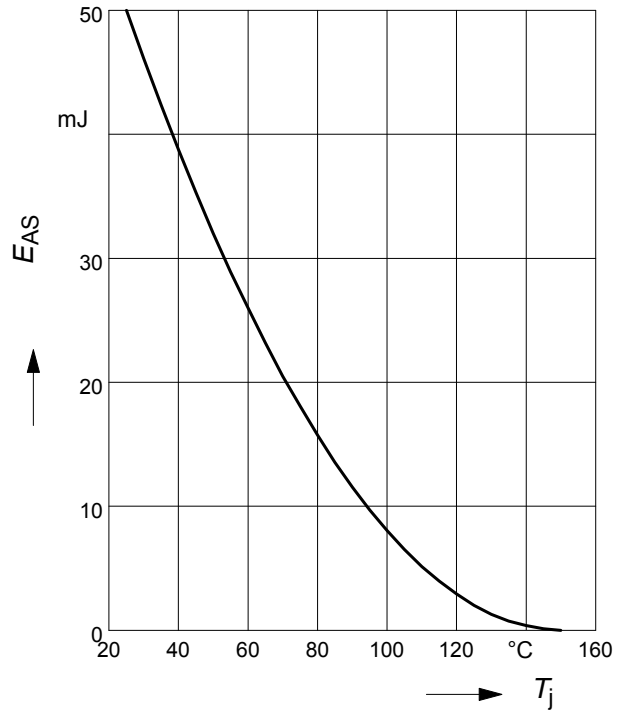
par.:  $T_j \leq 150\text{ }^\circ\text{C}$



**18 Avalanche energy**

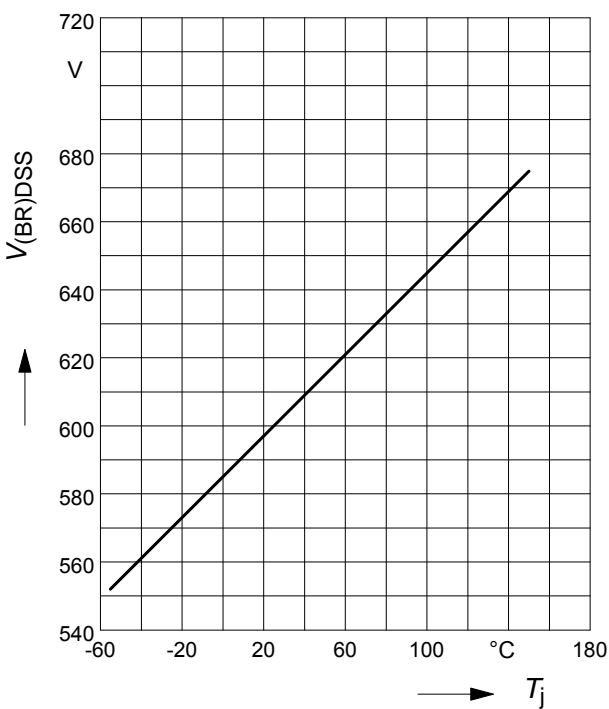
$E_{AS} = f(T_j)$

par.:  $I_D = 1.35\text{ A}$ ,  $V_{DD} = 50\text{ V}$



**19 Drain-source breakdown voltage**

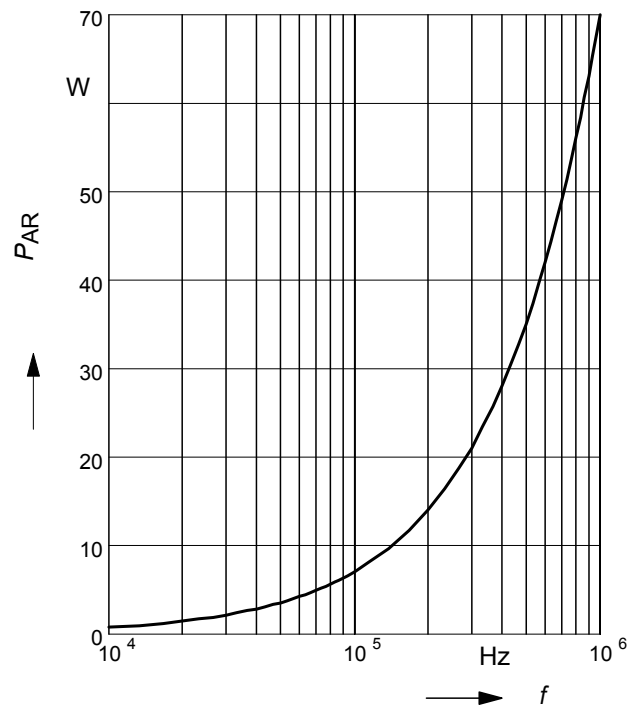
$V_{(BR)DSS} = f(T_j)$



**20 Avalanche power losses**

$P_{AR} = f(f)$

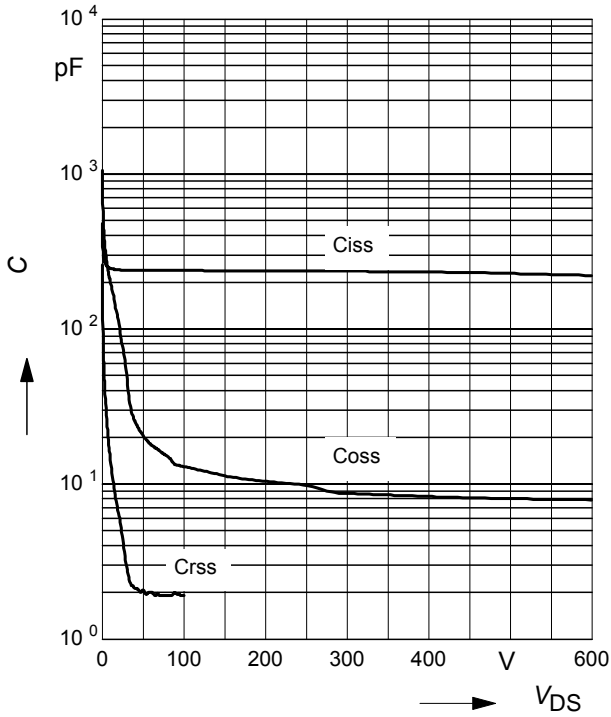
parameter:  $E_{AR} = 0.07\text{ mJ}$



**21 Typ. capacitances**

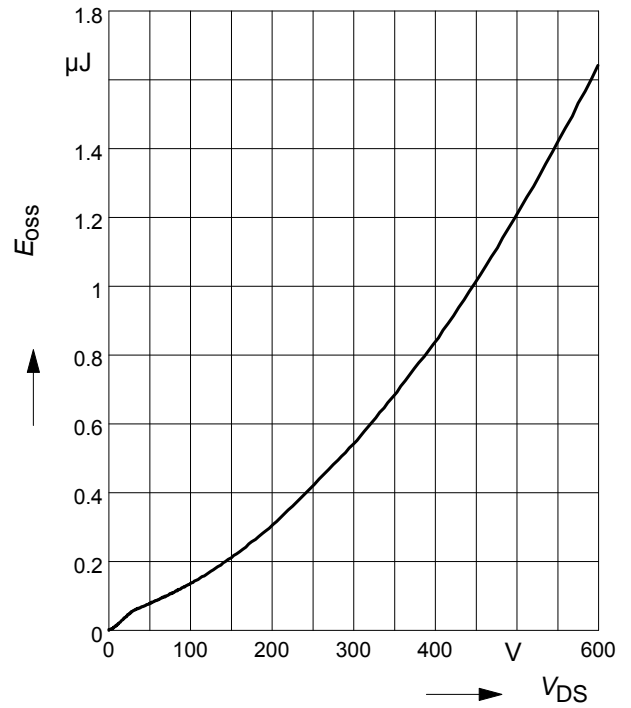
$C = f(V_{DS})$

parameter:  $V_{GS}=0V, f=1\text{ MHz}$

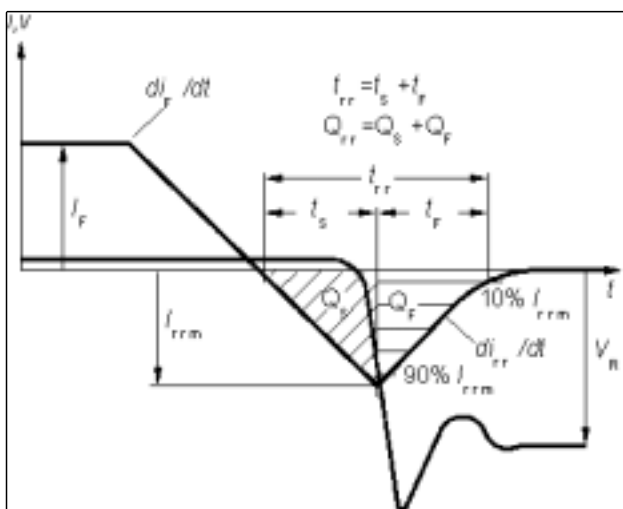


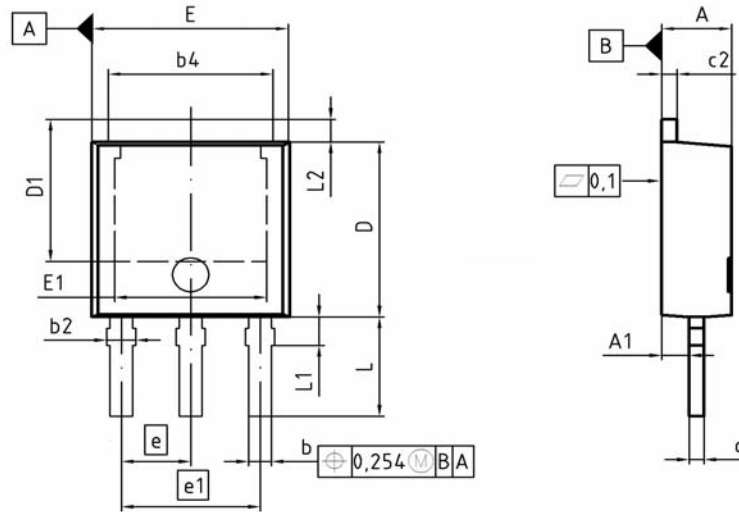
**22 Typ. C<sub>OSS</sub> stored energy**

$E_{Oss} = f(V_{DS})$



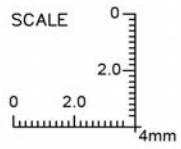
**Definition of diodes switching characteristics**

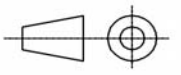




DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.39	0.086	0.094
A1	0.80	1.14	0.031	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.58	0.018	0.023
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.44	0.198	0.214
E	6.35	6.73	0.250	0.265
E1	4.90	5.10	0.193	0.201
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	3.40	3.60	0.134	0.142
L1	0.90	1.10	0.035	0.043
L2	0.90	1.10	0.035	0.043

DOCUMENT NO.  
Z8B00003329

SCALE 

EUROPEAN PROJECTION 

ISSUE DATE  
17-01-2008

REVISION  
03

Dimensions in mm/ inches

**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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